



ON Semiconductor®

BAV99

200 mA 70 V High Conductance Ultra-Fast Switching Diode

Features

- High Conductance: $I_F = 200 \text{ mA}$
- Fast Switching Speed: $t_{rr} < 6 \text{ ns}$ Maximum
- Small Plastic SOT-23 Package
- Series-Pair Configuration

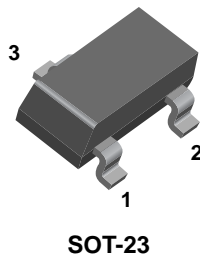
Applications

- High-Speed Switching Applications

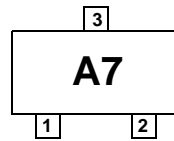
Description

The BAV99 is a 350 mW high-speed switching diode array with series-pair diode configuration. It achieves high-current conductivity, up to 200 mA, in a very small 7mm^2 footprint. These features make the BAV99 optimal for area-constrained applications that need a little extra power capability.

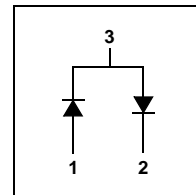
For common cathode and common anode high-speed switching diodes, explore Fairchild's BAV70 and BAW56. Looking for more options in the SOT-23 package? Check Fairchild's MMBD family.



SOT-23



Connection Diagram



Ordering Information

Part Number	Marking	Package	Packing Method
BAV99	A7	SOT-23 3L	Tape and Reel, Reel 7 inch
BAV99-D87Z	A7	SOT-23 3L	Tape and Reel, Reel 13 inch

Absolute Maximum Ratings⁽¹⁾

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
V_{RRM}	Maximum Repetitive Reverse Voltage	70	V
$I_{F(AV)}$	Average Rectified Forward Current	200	mA
I_{FSM}	Non-Repetitive Peak Forward Surge Current	Pulse Width = 1.0 Second	1.0
		Pulse Width = 300 Microseconds	8.0
T_{STG}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Note:

- These ratings are based on a maximum junction temperature of 150°C .
These are steady-state limits. ON Semiconductor should be consulted on applications involving pulsed or low-duty cycle operations.

Thermal Characteristics⁽²⁾

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
P_D	Power Dissipation	350	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	$^\circ\text{C}/\text{W}$

Note:

- PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

Electrical Characteristics

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Max.	Unit
V_R	Breakdown Voltage, per Diode	$I_R = 100 \mu\text{A}$	70		V
V_F	Forward Voltage, per Diode	$I_F = 1 \text{ mA}$		715	mV
		$I_F = 10 \text{ mA}$		855	
		$I_F = 50 \text{ mA}$		1.00	V
		$I_F = 150 \text{ mA}$		1.25	
I_R	Reverse Leakage, per Diode	$V_R = 70 \text{ V}$		2.5	μA
		$V_R = 25 \text{ V}, T_A = 150^\circ\text{C}$		30.0	
		$V_R = 70 \text{ V}, T_A = 150^\circ\text{C}$		50.0	
C_T	Total Capacitance, per Diode	$V_R = 0 \text{ V}, f = 1.0 \text{ MHz}$		1.5	pF
t_{rr}	Reverse-Recovery Time, per Diode	$I_F = I_R = 10 \text{ mA},$ $I_{RR} = 1 \text{ mA},$ $R_L = 100 \Omega$		6.0	ns

Typical Performance Characteristics

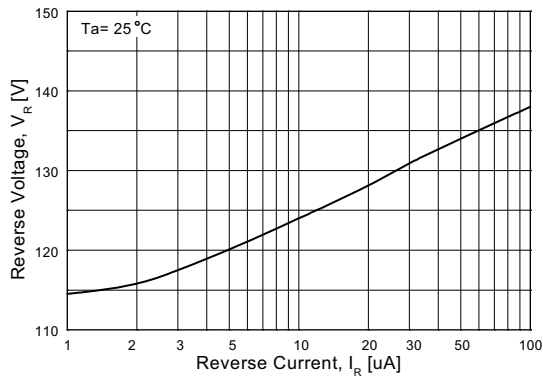


Figure 1. Reverse Voltage vs. Reverse Current

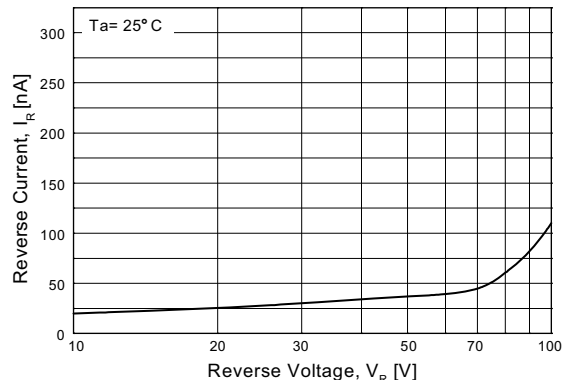


Figure 2. Reverse Current vs. Reverse Voltage

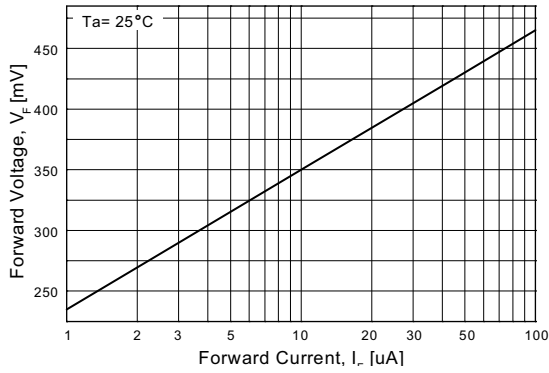


Figure 3. Forward Voltage vs. Forward Current
 V_F - 1 to 100 μ A

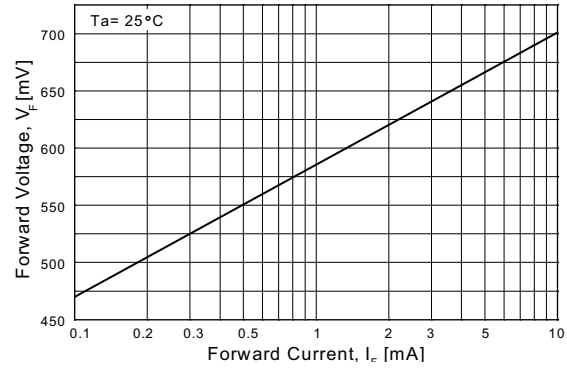


Figure 4. Forward Voltage vs. Forward Current
 V_F - 0.1 to 10 mA

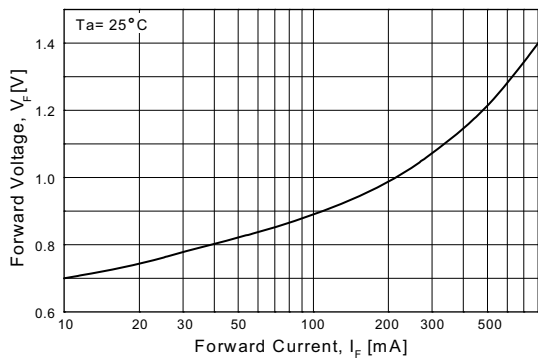


Figure 5. Forward Voltage vs. Forward Current
 V_F - 10 to 800 mA

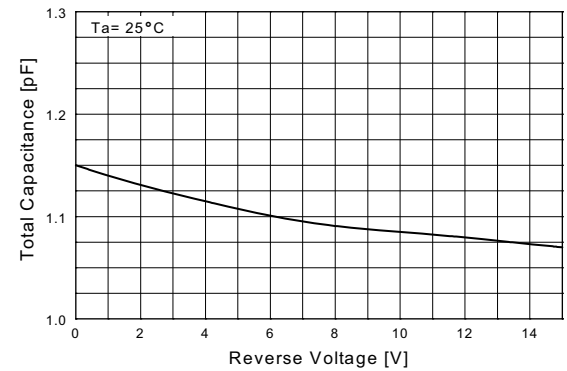


Figure 6. Total Capacitance vs. Reverse Voltage

Typical Performance Characteristics (Continued)

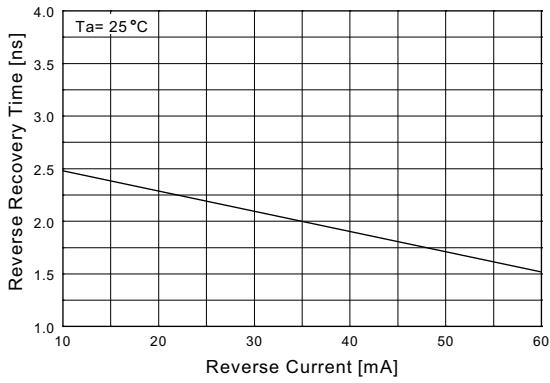


Figure 7. Reverse-Recovery Time vs. Reverse Current

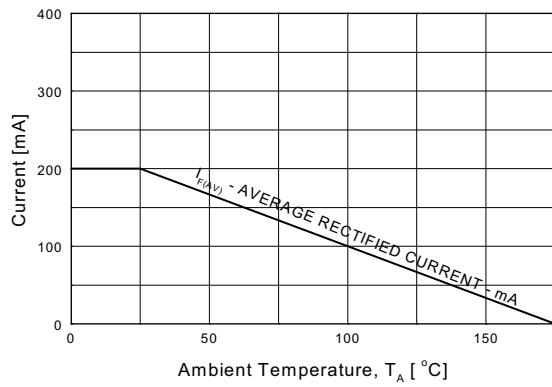


Figure 8. Average Rectified Current ($I_{F(AV)}$) vs. Ambient Temperature (T_A)

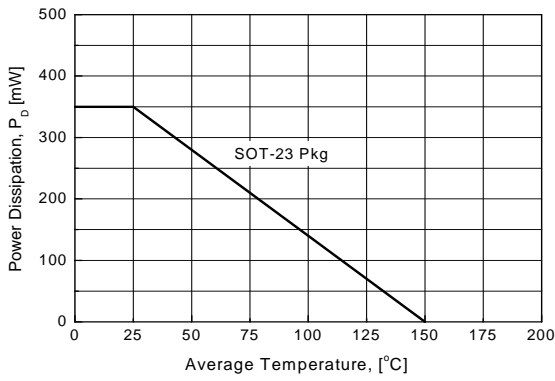
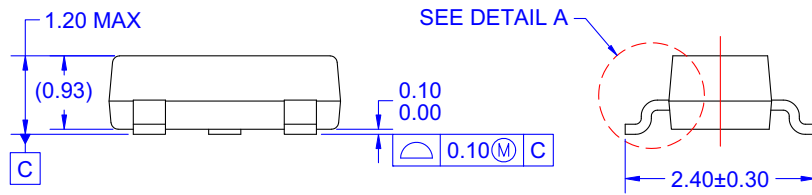
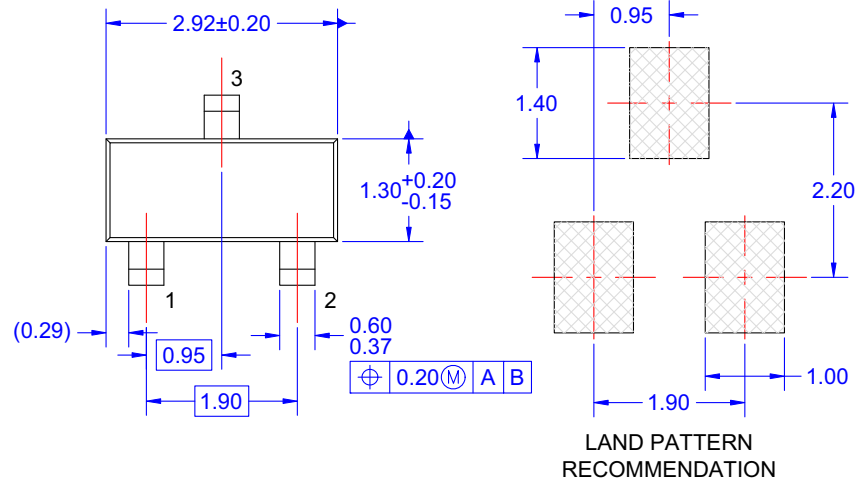


Figure 9. Power Derating Curve

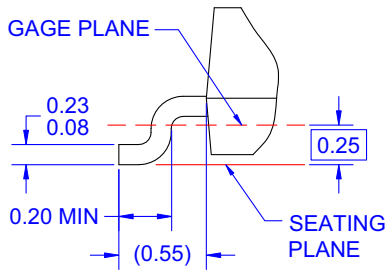
Physical Dimensions

SOT-23



NOTES: UNLESS OTHERWISE SPECIFIED

- A) REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE H.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE INCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
- D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M - 1994.
- E) DRAWING FILE NAME: MA03DREV10



DETAIL A
SCALE: 2X

Figure 10. 3-LEAD, SOT23, JEDEC TO-236, LOW PROFILE

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